

Dual High-Voltage Schottky Rectifiers

REV:1.01

Product Character

- ◆ Half Bridge Rectified、Common Cathode Structure.
- ◆ Multilayer Metal -Silicon Potential Structure.
- ◆ Low Power Waste, High Efficiency.
- ◆ Beautiful High Temperature Character.
- ◆ Have Over Voltage protect loop, high reliability.
- ◆ RoHs Product.

Typical Reference Data

VRRM= 80V
IF(AV)= 10A

VRRM= 90V
IF(AV)= 10A

VRRM= 100V
IF(AV)= 10A

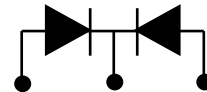
Primary Use

- Low Voltage High Frequency Switching Power Supply.
- Low Voltage High Frequency Invers Circuit.
- Low Voltage Continued Circuit and Protection Circuit.

Summarize

■ MBR1080、MBR1090、MBR10100 Schottky diode, in the manufacture uses the main process technology includes: Silicon epitaxial substrate, P+ loop technology, The potential metal and the silicon alloy technology, the device uses the two chip, the common cathode, the plastic package structure.

Polarity



Absolute Maximum Ratings

Item	Symbol	MBR1080	MBR1090	MBR10100	Unit
Maximal Inverted Repetitive Peak Voltage	VRRM	80	90	100	V
Maximal DC Interdiction Voltage	VDC	80	90	100	V
Average Rectified Forward Current TC=150°C Whole Device	IFAV	10			A
Unilateral		5			
Forward Peak Surge Current (Rated Load 8.3 Half Mssine Wave-According to JEDEC Method)	IFSM	150			A
Operating Junction Temperature	TJ	-40- +175			°C
Storage Temperature	TSTG	-40- +175			°C

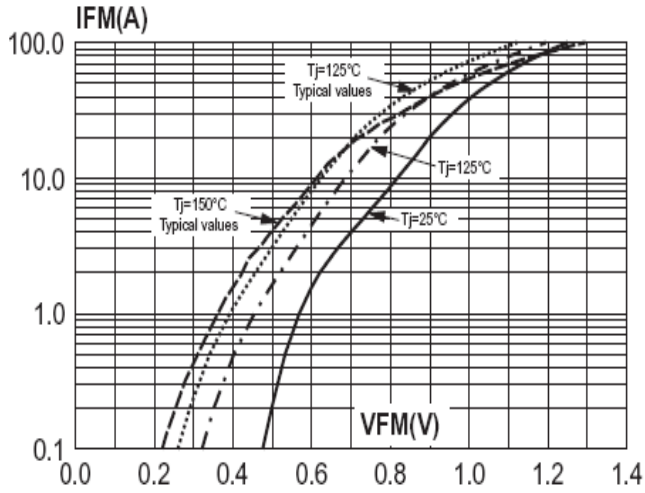
Electricity Character

Item	Test Condition	Minimum	Representative	MBR1080	MBR1090	MBR10100	Unit
IR	TJ =25°C	VR=VRRM		100			uA
	TJ =125°C			1			mA
VF	TJ =25°C	IF=5A		0.83	0.86	0.88	V

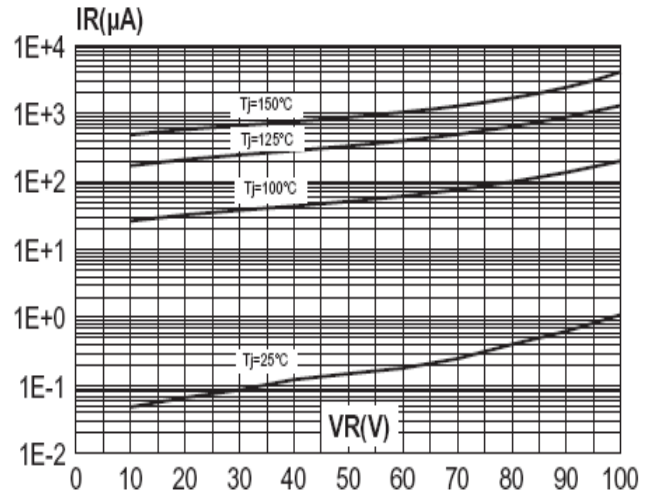
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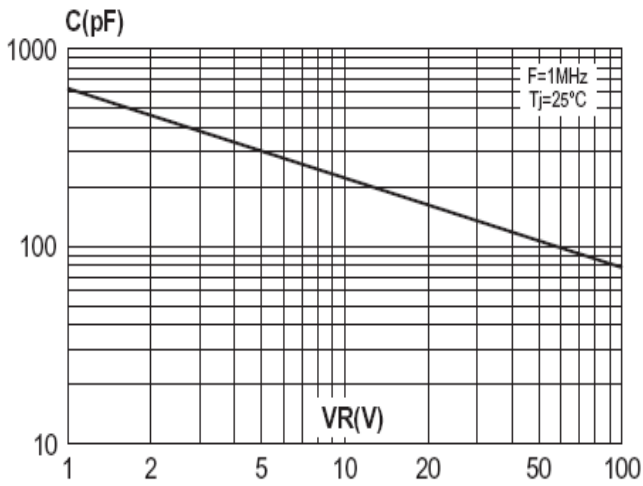
The forward voltage and forward current curve



The reverse leak current and the reverse voltage (single-device) curve



The crunode capacitance curve



ITO-220AB

